Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier in a SOT429N (TO247) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

2. Features and benefits

- · High thermal cycling performance
- · Planar passivated for voltage ruggedness and reliability
- · High voltage capacity
- · Very high current surge capability

3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- · Traction battery charging

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	1200	V
V_{RRM}	repetitive peak reverse voltage		-	-	1200	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	-	1100	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	-	-	1210	Α
Tj	junction temperature		-	-	150	°C
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 117 °C	-	-	80	A
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 117 ^{\circ}\text{C}$; $\overline{\text{Fig. 1}}$; $\overline{\text{Fig. 2}}$; $\overline{\text{Fig. 3}}$	-	-	126	A

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characte	Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7; Fig. 8}$		-	-	70	mA	
Dynamic chara	acteristics							
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 800 V; T_j = 125 °C; R_{GK} = 100 Ω; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform		1500	-	-	V/µs	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		A -
2	А	anode		G sym037
3	G	gate		Symoon
mb	A	mounting base; connected to anode	1 2 3 TO-247 (SOT429N)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT158W-1200T	TO-247	Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247	SOT429N			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1200	V
V_{RRM}	repetitive peak reverse voltage		-	1200	V
I _{T(AV)}	average on-state current	half sine wave; T _{mb} ≤ 117 °C	-	80	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{mb} \le 117 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	126	A
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	1100	A
		half sine wave; T _{j(init)} = 25 °C; t _p = 8.3 ms	-	1210	Α
l ² t	I ² t for fusing	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; no voltage reapplied	-	6115	A²s
dl _T /dt	rate of rise of on-state current	I _G = 200 mA	-	150	A/µs
I _{GM}	peak gate current		-	8	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	20	W
P _{G(AV)}	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

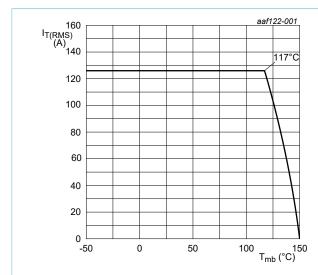


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

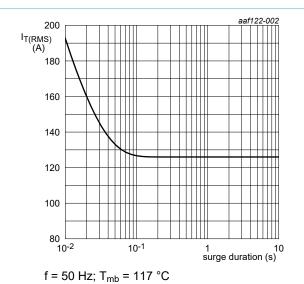


Fig. 2. RMS on-state current as a function of surge duration; maximum values

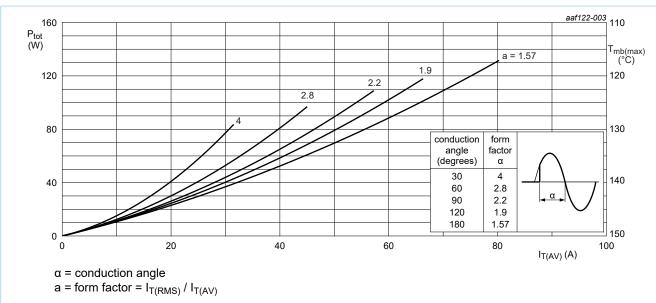


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

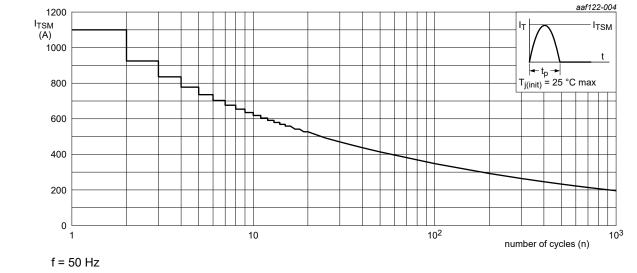
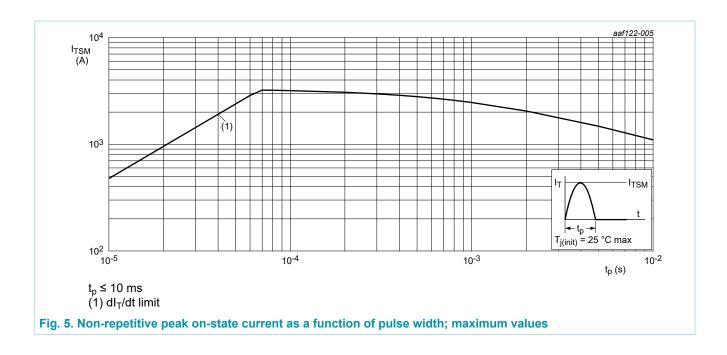


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	0.25	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

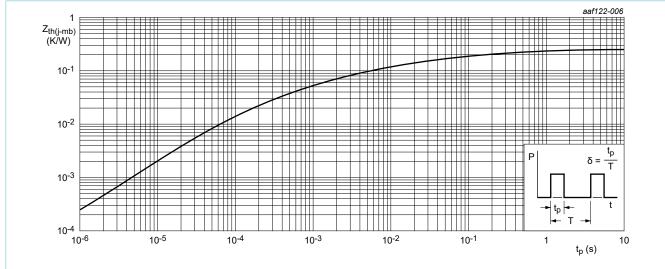


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7;$ Fig. 8	-	-	70	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 9$	-	-	300	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	200	mA
V _T	on-state voltage	I _T = 80 A; T _j = 25 °C; <u>Fig. 11</u>	-	-	1.35	V
		I _T = 160 A; T _j = 25 °C; <u>Fig. 11</u>	-	-	1.65	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 12	-	0.7	1	V
		$V_D = 800 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 12	0.25	0.4	-	V
I _D	off-state current	V _D = 1200 V; T _j = 125 °C	-	-	3	mA
I _R	reverse current	V _R = 1200 V; T _j = 125 °C	-	-	3	mA
Dynamic c	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 800 V; T_j = 125 °C; R_{GK} = 100 Ω ; (V_{DM} = 67% of V_{DRM}); exponential waveform	1500	-	-	V/µs
		V_{DM} = 800 V; T_{j} = 150 °C; R_{GK} = 100 Ω ; (V_{DM} = 67% of V_{DRM}); exponential waveform	1000	-	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 40 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/µs; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 804 V; T_j = 125 °C; I_{TM} = 20 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	150	-	μs

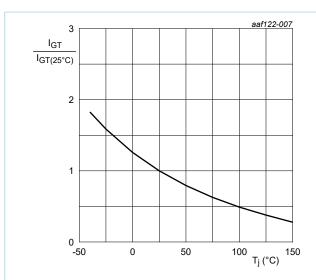


Fig. 7. Normalized gate trigger current as a function of junction temperature

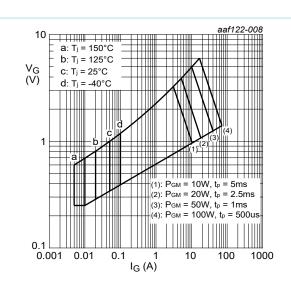


Fig. 8. Gate voltage as a function of gate current

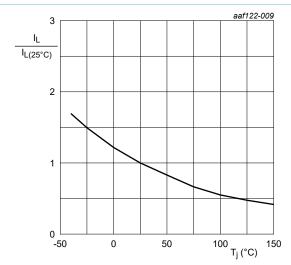


Fig. 9. Normalized latching current as a function of junction temperature

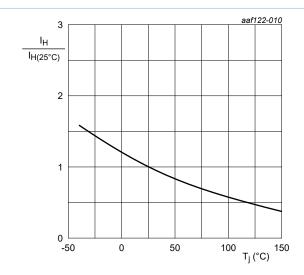
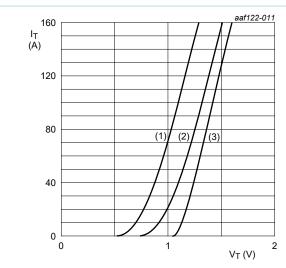


Fig. 10. Normalized holding current as a function of junction temperature



 V_o = 0.984 V; R_s = 0.0033 Ω (1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values (3) T_j = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

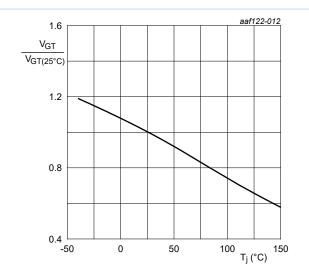


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

10. Package outline

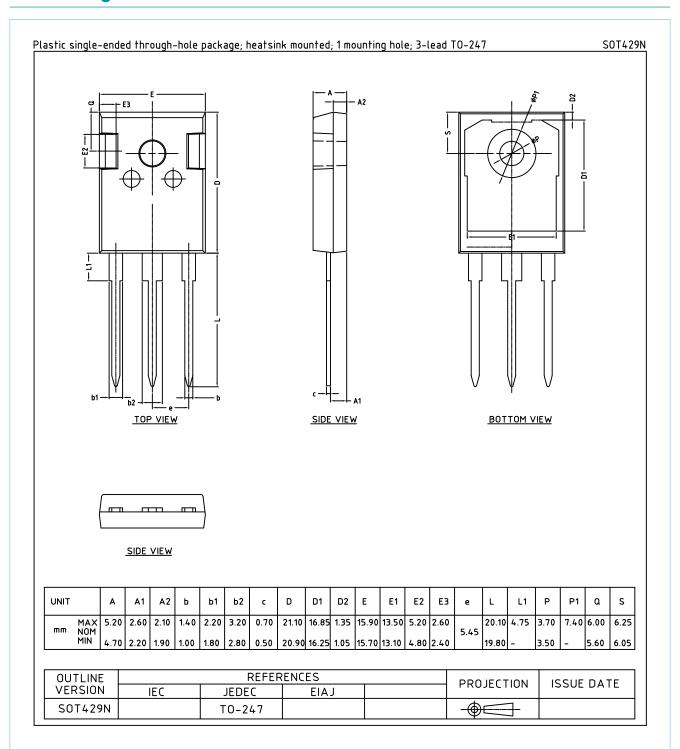


Fig. 13. Package outline TO-247 (SOT429N)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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